

SMP600G-FM

MECHANICAL DATA

Dimensions in mm.

WINDOW Ø 8.1 ± 0.2 Ø 8.1 ± 0.1 SENSITIVE SURFACE Ø 0.45 LEAD 5.08 ± 0.2

TO-39 Package

Pin 1 – Anode Pin 2 – Cathode Pin 3 – Case

P.I.N. PHOTODIODE

FEATURES

- HIGH SENSITIVITY
- VISIBLE AND UV BLIND
- PHOTODIODE ISOLATED FROM PACKAGE
- EXCELLENT LINEARITY
- LOW NOISE
- WIDE SPECTRAL RESPONSE
- RG850 INTEGRAL OPTICAL FLTER
- TO39 HERMETIC METAL CAN PACKAGE
- EMI SCREENING MESH AVAILABLE

DESCRIPTION

The SMP600G-FM is a Silicon P.I.N. photodiode incorporated in a hermetic metal can package. The electrical terminations are via two leads of diameter 0.018" on a pitch centre diameter of 0.2". The can structure incorporates an optical filter that only transmits infra-red light. The photodiode is electrically isolated from the package, which has a separate earth lead.

The larger photodiode active area provides greater sensitivity than the SMP550 range of devices, with a slight reduction in speed. Inherent in the device geometry is a reduction in the receiving angle. The photodiode structure has been optimised for high sensitivity, light measurement applications. The metal can, isolated photodiode and optional screening mesh ensure a rugged device with a high degree of immunity to conducted and radiated electrical interference.

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

Operating temperature range		-40°C to +70°C	
Storage temperatur	e range	-45°C to +80°C	
Temperature coeffic	cient of responsively	0.35% per °C	
Temperature coeffic	cient of dark current	x2 per 8°C rise	
Reverse breakdowr	n voltage	60V	
		4	

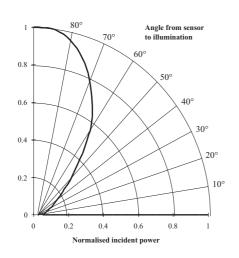


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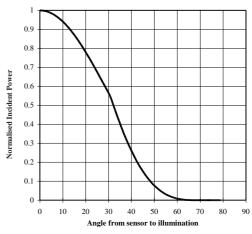
CHARACTERISTICS (T_{amb}=25°C unless otherwise stated)

Characteristic	Test Conditions.		Min.	Тур.	Max.	Units	
Responsively	λ at 900nm		0.45	0.55		A/W	
Active Area				15		mm²	
Dark Current	E = 0 Dark	1V Reverse		2	6	nA	
Dark Guilent	E = 0 Dark	10V Reverse					
Breakdown Voltage	E = 0 Dark	10µA Reverse	60	80		V	
Capacitance	E = 0 Dark	0V Reverse		90		pF	
Capacitance	E = 0 Dark	20V Reverse		25			
Rise Time	30V Reverse			12		ns	
IXISE TITLE	50Ω			12			
NEP	900nm			20x10 ⁻¹⁴	0.45	W/√Hz	

Directional characteristics



Directional Characteristics



Spectral Response

